	Application No.	Applicant(s)
Notice of Allowability	09/880,223	HSU ET AL.
	Examiner	Art Unit
	Steven H. Rao	2814
The MAILING DATE of this communication appeall claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RI of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in this apport of other appropriate communication GHTS. This application is subject to	plication. If not included will be mailed in due course. THIS
1. This communication is responsive to <u>10/08/04</u> .		·
2. The allowed claim(s) is/are 12 and 15-17.		
3. X The drawings filed on 19 February 2003 are accepted by the	ne Examiner.	
 Acknowledgment is made of a claim for foreign priority under a) All b) Some* c) None of the: Certified copies of the priority documents have Certified copies of the priority documents have Copies of the certified copies of the priority documents have International Bureau (PCT Rule 17.2(a)). * Certified copies not received: Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONM THIS THREE-MONTH PERIOD IS NOT EXTENDABLE. 	been received. been received in Application No cuments have been received in this of this communication to file a reply	national stage application from the
5. A SUBSTITUTE OATH OR DECLARATION must be subminFORMAL PATENT APPLICATION (PTO-152) which give		
 6. CORRECTED DRAWINGS (as "replacement sheets") muss (a) including changes required by the Notice of Draftspers 1) hereto or 2) to Paper No./Mail Date (b) including changes required by the attached Examiner's Paper No./Mail Date Identifying indicia such as the application number (see 37 CFR 1. each sheet. Replacement sheet(s) should be labeled as such in the DEPOSIT OF and/or INFORMATION about the deposit attached Examiner's comment regarding REQUIREMENT 	on's Patent Drawing Review (PTO- c. Amendment / Comment or in the Co. 84(c)) should be written on the drawing the header according to 37 CFR 1.121(c) sit of BIOLOGICAL MATERIAL re	Office action of ngs in the front (not the back) of d). nust be submitted. Note the
Attachment(s) 1. Notice of References Cited (PTO-892) 2. Notice of Draftperson's Patent Drawing Review (PTO-948) 3. Information Disclosure Statements (PTO-1449 or PTO/SB/0 Paper No./Mail Date 4. Examiner's Comment Regarding Requirement for Deposit of Biological Material	6. Interview Summary Paper No./Mail Date 8), 7. Examiner's Amendr	te

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Response to Amendment.

Applicants' supplemental amendment faxed on October 08, 2004 has been entered on October 08, 2004.

Therefore claim 12 as amended by the Supplemental amendment and claims 15-17 as previously recited are currently pending in the Application.

Claims 1-11, 13-14 and 18-31 have been cancelled.

Reasons for allowance

Claims 12 and 15-17 are allowed.

The following is an examiner's statement of reasons for allowance:

The prior art taken either singularly or in combination fails to anticipate or fairly suggest the limitation of the dependent claims, in such manner that a rejection under 35 U.S.C. 102 or 103 would be proper. The prior art fails to teach a combination of all the claimed features as presented in independent claims, which include An array of planar T-Ram cells comprising: a plurality of T-ORam cells, said plurality of T-Ram cells being arranged in an array and fabricated over a substrate, each of said plurality of T-RAM cells including a buried vertical thyristor and a horizontally stacked pseudo-TFT transfer gate having a body of a majority portion of single crystalline material using a n+ layer below it as seed material by a epitaxial lateral overgrowth technique, said horizontally stacked pseudo-TFT transfer gate including a source/drain and body, said thyristor being buried underneath said horizontally stacked pseudo-TFT transfer gate, wherein said horizontally stacked pseudo-TFT transfer gate covers at least a portion of said thyristor, and further wherein the top surface of said horizontally stacked pseudo-TFT

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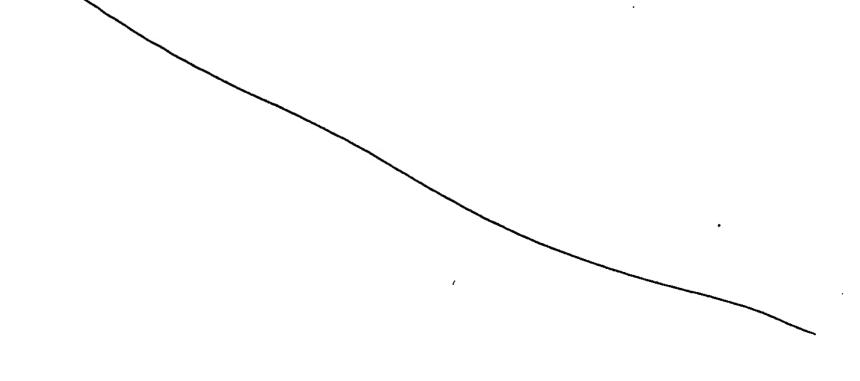
transfer gate forma a coplanar top surface of each of said horizontally stacked pseudo-TFT transfer gate of each said T-RAM cell wherein each of the plurality of T-Ram cells has a size of less than a size of less than or equal to 6 F².

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

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Any inquiry concerning this communication or earlier communications from the examiner should be directed to Steven H. Rao whose telephone number is (571) 272-1718. The examiner can normally be reached on 8.00 to 5.00.

The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.



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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Steven H .Rao

Patent Examiner

October 14, 2004

LONG PHAM PRIMARY EXAMINER